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Silicon NPN transistor in a SOT-23 Plastic Package.

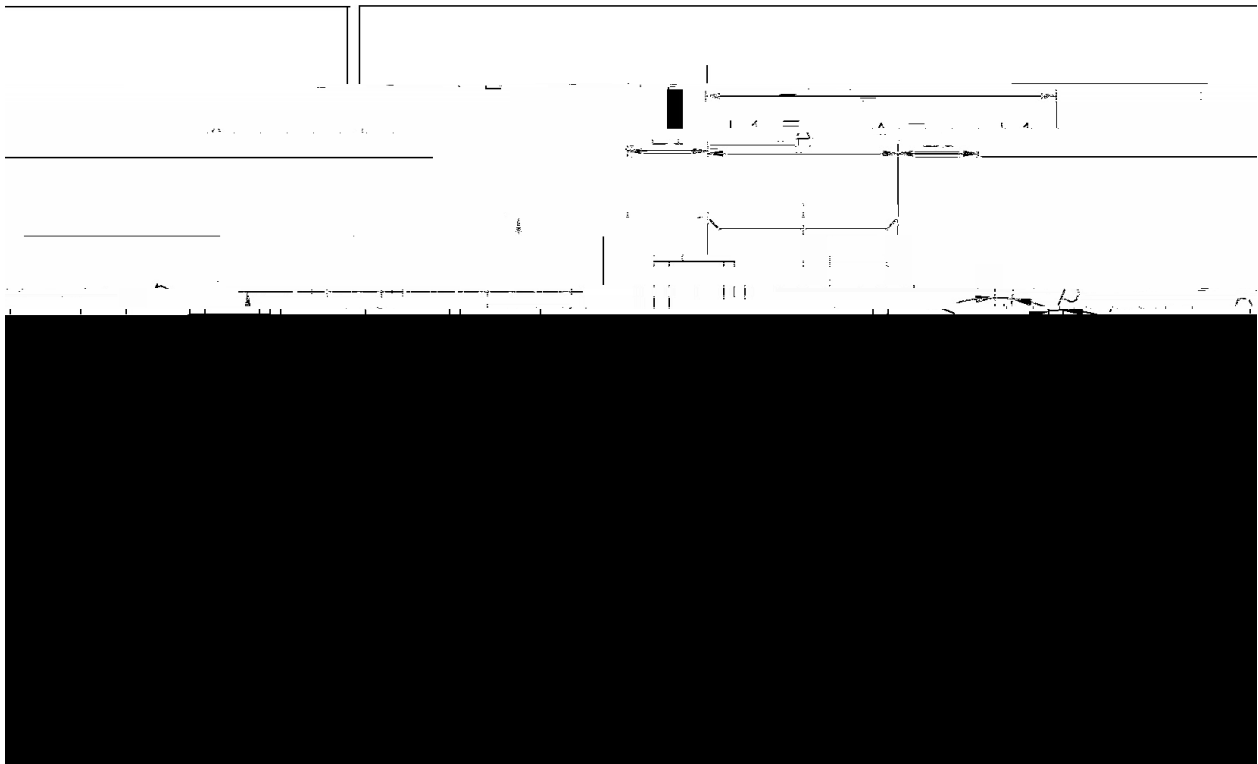
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	40			V
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			50	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=6.0V$ $I_C=0$			50	nA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=150mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=500mA$	40			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=10mA$	80			
	$h_{FE(4)}$	$V_{CE}=1.0V$ $I_C=1.0mA$	40			
	$h_{FE(5)}$	$V_{CE}=1.0V$ $I_C=0.1mA$	20			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$					

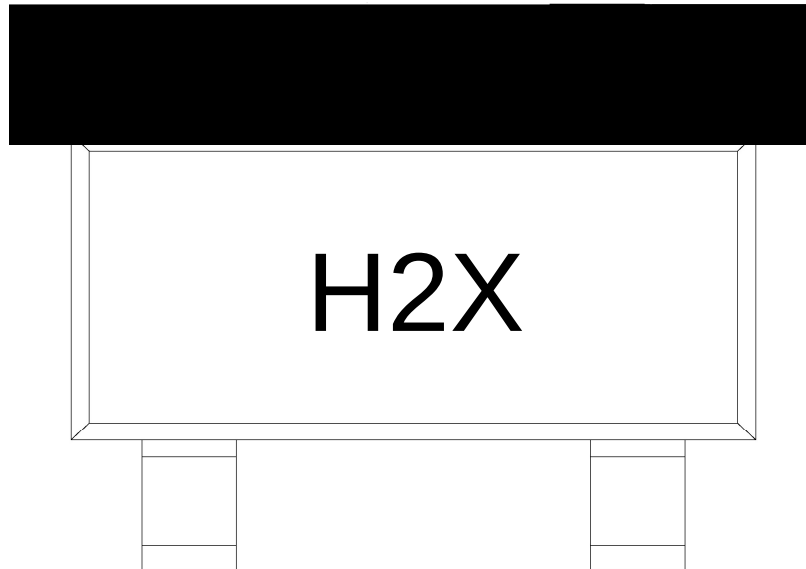
/ Package Dimensions

MMBT4401 is a 3-pin, 1.5mm pitch, SMD package. The package is shown in the following diagram.



Dimensions In Millimeters	Symbol	Dimensions In Millimeters	Symbol	Dimension
0.8	MB	Max	C	1.30Max
1.25	2.2	2.7	D	0.80
0.45	0.45	0.45	E	1.50
0.30	0.30	0.30	F	0.30
0.30	0.30	0.30	G	0.30
0.30	0.30	0.30	H	0.30
0.30	0.30	0.30	I	0.30
0.30	0.30	0.30	J	0.30
0.30	0.30	0.30	K	0.30
0.30	0.30	0.30	L	0.30
0.30	0.30	0.30	M	0.30
0.30	0.30	0.30	N	0.30
0.30	0.30	0.30	O	0.30
0.30	0.30	0.30	P	0.30
0.30	0.30	0.30	Q	0.30
0.30	0.30	0.30	R	0.30
0.30	0.30	0.30	S	0.30
0.30	0.30	0.30	T	0.30
0.30	0.30	0.30	U	0.30
0.30	0.30	0.30	V	0.30
0.30	0.30	0.30	W	0.30
0.30	0.30	0.30	X	0.30
0.30	0.30	0.30	Y	0.30
0.30	0.30	0.30	Z	0.30

/ Marking Instructions



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2X

Note:

H Company Code

2X Product Type Code



() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1 150 180 60 90sec;
- 2 245±5 5±0.5sec;

1.Preheating:150~180°C, Time:60~90sec.